
SiGe, Ge, and Related Compounds: Materials, Processing, and Devices 11: In Memory of Qizhi Liu

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Table of Contents

<i>Preface</i>	<i>iii</i>
<i>(Invited) Mobility Enhancement Technology of Extremely-Thin Body Ge-on-Insulator Channel Mosfets</i> <i>S. Takagi, X. Han, C. T. Chen, K. Sumita, K. Toprasertpong, M. Takenaka</i>	3
<i>(Keynote) Epitaxial Si/SiGe Multi-Stacks: From Stacked Nano-Sheet to Fork-Sheet and CFET Devices</i> <i>R. Loo, A. Akula, Y. Shimura, C. Porret, E. Rosseel, T. Dursap, A. Y. Hikavy, M. Beggiato, J. Bogdanowicz, A. Merkulov, M. Ayyad, H. Han, O. Richard, A. Impagnatiello, D. Wang, K. Yamamoto, T. Sipócz, Á. Kerekes, H. Mertens, N. Horiguchi, R. Langer</i>	15
Source/Drain Epitaxy for Nanosheet-Based CFET Devices <i>E. Rosseel, C. Porret, T. Dursap, R. Loo, H. Mertens, J. Ganguly, R. Sarkar, C. Cavalcante, O. Richard, J. Geypen, B. Marozas, D. Casey, R. Khazaka, S. Demuyne, L. P. B. Lima, R. Langer, S. Biesemans, N. Horiguchi</i>	29
Low-Temperature Selective Si:As Epitaxy <i>D. Abdula, Y. Chiu, B. Marozas, R. Khazaka, C. K. Miskin, J. S. Lee, A. T. Demos</i>	37
Defect-Free SiGe/Si Multistacks for Next-Generation CFET Architectures <i>G. Rengo, D. Casey, B. Marozas, N. Claessens, R. Khazaka</i>	47
An Assessment of the Lateral Selective Etching, with HCl, of High Versus Low Ge Content SiGe Layers <i>J. M. Hartmann, B. Previtali, F. Aussenac, P. Dezest, O. Glorieux, A. Blot-Saby, L. Couture, S. Barraud</i>	55

Design of PNP SiGe HBTs Towards 200 GHz f_{max} <i>U. Raghunathan, S. Shank, S. McTaggart, M. Lydon-Nuhfer, C. Luce, R. Hazbun, S. Bosley, A. Vallett, D. Dillon, S. Sirohi, J. B. Johnson, A. Derrickson, V. Jain, J. J. Pekarik</i>	75
Improved Nonlinear Self-Heating Compact Modeling in SiGe HBTs Using Mextram <i>A. Zhang, G. Niu, Y. Li, M. Willemsen, A. Scholten</i>	83
(Invited) Epitaxial Process Development and Challenges for Advanced SiGe BiCMOS <i>F. Deprat, J. Vives, A. Gauthier, M. Frauenrath, J. Lespiaux, S. Verdier, A. Ferrandon, E. Oudot, P. G. Ribot, P. Chevalier</i>	93
(Invited) Advancing Si Spin Qubit Research: Process Integration of Hall Bar FETs on Si/SiGe in a 200mm BiCMOS Pilot Line <i>F. Reichmann, A. Mistrioni, Y. Yamamoto, P. Kulse, S. Marschmeyer, D. Wolansky, O. Fursenko, M. H. Zöllner, G. Capellini, L. Diebel, D. Bougeard, M. Lisker</i>	109
Low Disorder and High Mobility 2DEG in Si/SiGe Fabricated in 200 mm BiCMOS Pilot line <i>A. Mistrioni, F. Reichmann, Y. Yamamoto, M. H. Zöllner, G. Capellini, L. Diebel, D. Bougeard, M. Lisker</i>	123
200 mm Wafer Level Characterization at 2 K of Si/SiGe Field-Effect Transistors <i>N. D. Komericki, P. Muster, F. Reichmann, T. Huckemann, D. Kaufmann, Y. Yamamoto, M. Lisker, W. Langheinrich, L. R. Schreiber, H. Bluhm, R. Quay</i>	133
The Lattice Strain Distribution in Ge_xSn_{1-x} Micro-Disks Investigated at the Sub 100-nm Scale <i>C. Corley-Wiciak, M. H. Zöllner, A. A. Corley-Wiciak, F. Rovaris, G. Sfruncia, G. Nicotra, I. Zaitsev, C. L. Manganelli, E. Zatterin, D. Spirito, A. Marzegalli, T. Schulli, N. Von Den Driesch, D. Buca, F. Montalenti, C. Richter, G. Capellini</i>	145
Light Emission of Sn/Ge MQW pin Diodes on Si <i>M. Oehme, M. Hack, L. Starz, H. Darwish, C. Spieth, S. C. Schaefer, M. Wanitzek, L. Seidel, E. Kasper, D. Schwarz</i>	155
Selective-Area Growth of InGaAs Nanowires on SOI and the Vertical Transistor Application <i>K. Taniyama, Y. Takeda, Y. Azuma, Z. Zheng, J. Motohisa, K. Tomioka</i>	165
Demonstration of VGAA-TFETs using InAs/Si Heterojunction on SOI substrate <i>Y. Takeda, Y. Azuma, Z. Zheng, J. Motohisa, K. Tomioka</i>	171

Photoemission Study on Si and Ge Segregation on Al/Si _{0.8} Ge _{0.2} Structures <i>T. Sakai, A. Ohta, N. Taoka, Y. Yamamoto, M. A. Schubert, S. Miyazaki, K. Makihara</i>	177
Advanced SiGe:B Raised Sources and Drains for p-type FD-SOI MOSFETs <i>J. M. Hartmann, F. Aussenac, O. Glorieux, D. Cooper, S. Kerdilès, Z. Chalupa, F. Boulard, H. Niebojewski, B. Duriez, T. Bordignon, S. Peru, P. Michałowski, R. Daubriac, F. Cristiano</i>	185
Optical Properties of Multilayered Staggered SiGe Nanodots Depending on Si Spacer Growth Temperature <i>Y. Ito, R. Yokogawa, W. C. Wen, Y. Yamamoto, A. Ogura</i>	207
Comprehensive study on epitaxial growth of GeSn(111) layers with high Sn content on Si(111) featuring Ge buffer layer <i>S. Shibayama, S. Mori, Y. Kato, M. Sakashita, M. Kurosawa, O. Nakatsuka</i>	215
Evaluation of Band Structure of Single Crystalline Si-Rich SiSn thin Film <i>H. Ishizaki, R. Yokogawa, Y. Ito, T. Minowa, M. Kurosawa, A. Ogura</i>	225
Development of Novel Ternary Alloy of CSiSn for Low-Cost Next Generation Photovoltaics <i>S. Banishashemian, M. Mahmoudi, A. Mosleh, H. Naseem</i>	233
Boron Delta-Doping in Si : B Stacks By RP-CVD Epitaxy <i>A. Ferrandon, F. Deprat, J. Vives, M. Frauenrath, V. Guyader, C. Lacomme, I. Madaci, L. Favre, I. Berbezier</i>	241
Selective Epitaxy of Tensile, Highly Doped SiP for Planar NMOS FD-SOI Devices <i>J. Kanyandekwe, J. M. Hartmann, J. Lespiaux, T. Marion, L. Saidi, V. Lapras, A. Bond, F. Bringuier, J. Richy, N. Gauthier, A. Thouvard, T. Biet, L. Couture, A. Blot-Saby, A. Andre, J. Marchand, C. Licitra, R. Coquand, A. Royer, T. Dewolf, H. Al Dujaili, A. Lassenberger, O. Glorieux</i>	253
Selective Epitaxial Growth of SiGe(:B) for Advanced p-Type Fd-SOI <i>J. Lespiaux, J. Kanyandekwe, T. Marion, L. Saidi, V. Lapras, A. Bond, F. Bringuier, J. Richy, A. Thouvard, T. Biet, E. Nolot, L. Couture, L. Brunet, P. Rodriguez, E. Dos Reis, N. Gauthier, A. Blot-Saby, J. M. Hartmann</i>	271

Developing the Metrology for Atomic Level Spatial Distribution and Local Chemistry Analysis of in-Situ Dopants By Atom Probe Tomography <i>J. R. Lin, R. J. H. Morris, J. E. Scheerder, A. Y. Hikavy, C. Porret, A. Vantomme, C. Fleischmann</i>	297
Polycrystalline inclusion-free growth of thick, lattice-matched SiGeC with high substitutional Carbon concentrations up to 2% <i>M. Frauenrath, J. Vives, M. Devaux, C. Blondel, E. Aybeke, B. Obeid, R. Duru, T. Levert, T. Printemps, S. Verdier, F. Deprat</i>	305
High Performance CMOS RF Switch Based on Highly Carbon Doped Raised Source/Drain Regions <i>A. Chollet, I. Berbezier, L. Favre, M. Labrot, J. Dura, K. Melhem, R. Duru, F. Figarols, M. Abel, S. Bodnar, B. Bartolotti</i>	317
Benchmarking of HCl-Based Cyclic Deposition / Etch (CDE) and Single Deposition / Etch (DE) Processes for Selective Epitaxial Growth of SiGeC:B Films <i>J. Vives, F. Deprat, M. Frauenrath, S. Verdier, E. Aybeke, A. Baron, E. Marque, D. Chaussende</i>	333
Piezo Electric Properties of Epitaxial SiGe <i>Y. Yamamoto, W. C. Wen, N. Inomata, A. A. Corley-Wiciak, D. Ryzhak, C. Corley-Wiciak, R. Sorge, B. Tillack, T. Ono, Z. Zhizian</i>	353
Reaxff MD Analysis of Substrate Material Properties into Oxide Films during Thermal Oxidation Process of Group IV Semiconductor Materials <i>K. Sekiguchi, N. Uene, D. Otori, K. Endo, T. Tokumasu</i>	363
Author Index	371